

Nanostructure Enhanced Terahertz Technology for Sensing and Imaging

Seongsin Margaret Kim, Babatunde Ajilore, Gang Shen, Dave Wilbert, and Patrick Kung

Supported by NSF DMR-0821704 and EEC-0824452

## **TERAHERTZ FOR SENSING AND IMAGING**

- > Material fundamental properties studies (metamaterials, quantum nonlinear dynamics)
- ➢ Biomedical imaging
- **Gas sensing, gas phase spectroscopy**
- Biological agent, explosive detection



Biomedical imaging, S.M. Kim et al, (2005)

#### <u>III-NITRIDE NANOSTRUCTURES</u> and COMPACT THz SOURCES

> Nanowires/rods have a significantly increased smooth emitting surface area Diameters can be on the order of the accumulation layer thickness.

#### Advantages of InGaN for THz:

- •Engineerable bandgap (λ=365~1775 nm)
- •High saturation & peak drift velocity
- Short carrier lifetime
- High breakdown electric field



**THz-TDS System:** Broadband THz signal upto **3THz** ≻High dynamic range

### NANOSTRUCTURE SYNTHESIS AND **CHARACTERIZATION**

- ► Unique custom designed MOVPE reactor Specifically designed for wide bandgap semiconductors and
- nanostructures



> The time-resolved photoinduced conductivity can be obtained from the differential terahertz

transmission

$$\begin{aligned} \left| \Delta \sigma(\tau) \right| &= \frac{1 + n_s}{\delta Z_0} \frac{\Delta T}{T} \\ T(\omega) &= \frac{E_s(\omega)}{E_r(\omega)} = \frac{|E_s(\omega)|}{|E_r(\omega)|} \frac{e^{i\phi_s(\omega)}}{e^{i\phi_r(\omega)}} \\ \Delta n(\omega) &= -\frac{cd}{\delta} \left[ \phi(\omega) - \phi(\omega) \right] \end{aligned}$$







>New method of nanomaterials Parkinson et al. (2007) characterization:charge transfer in photovoltaic solar cell

# **THz NANOSTRUCTURE CHARACTERIZATION**

Being a non-contact optical method, THz time domain spectroscopy is an ideal method to characterize the electrical properties of semiconductor nanostructures, including carrier densities and conductivity.



Parkinson et al, Nano Lett. (2007) A. Huber et al, Nano Lett. (2008) The time-resolved photoinduced conductivity can be obtained from the differential terahertz transmission

$$|\Delta\sigma(\tau)| = \frac{1+n_s}{\delta Z_0} \frac{\Delta T}{T}$$

$$T(\omega) = \frac{E_s(\omega)}{E_r(\omega)} = \frac{|E_s(\omega)|}{|E_r(\omega)|} \frac{e^{i\phi_s(\omega)}}{e^{i\phi_r(\omega)}}$$

$$\alpha(\omega) = -\frac{2}{rd} \ln \frac{|E_s(\omega)|}{|E_r(\omega)|}$$

$$\Delta n(\omega) = -\frac{cd}{\omega} \left[\phi_s(\omega) - \phi_r(\omega)\right]$$

100 nm



- Application of various THz spectroscopy technology
- New method of nanomaterials characterization:
  - -Nanomagnetic materials, spintronic devices
  - -Probe for charge transfer in photovoltaic solar cells
  - -Carbon Nanotube